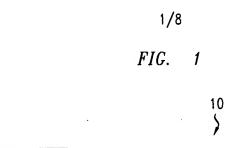


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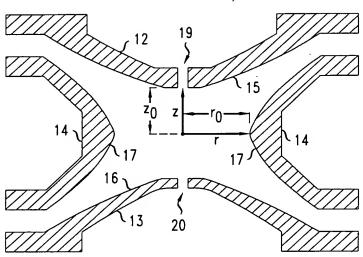
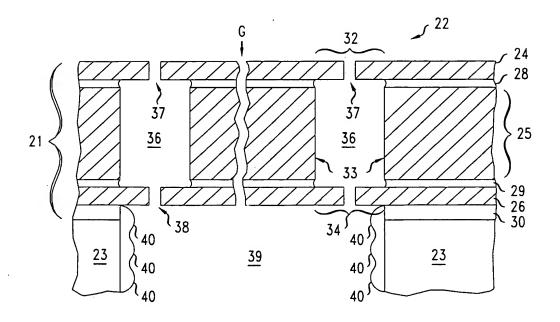
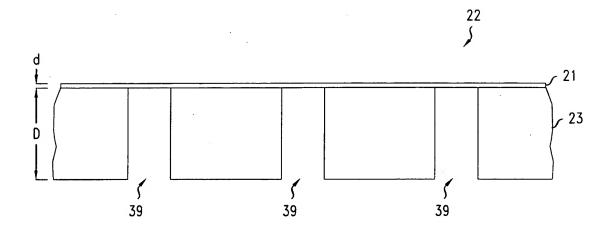


FIG. 2A



*FIG.* 2 B



*FIG.* 2 C

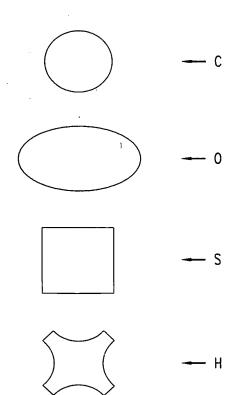


FIG. 3

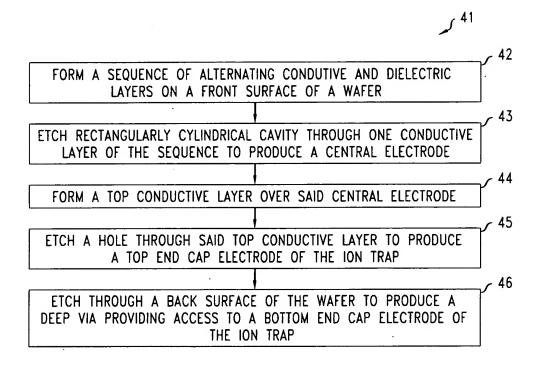
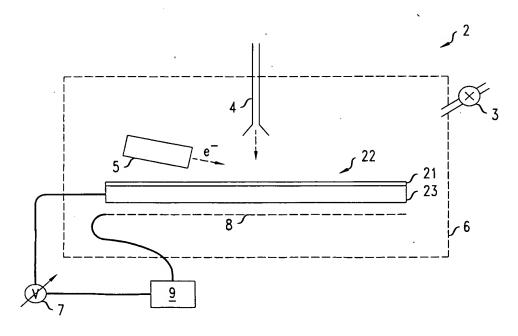


FIG. 4



## *FIG.* 5

50 كىر PERFORM DEPOSITIONS TO FORM A SEQUENCE THAT INCLUDES AN AI LAYER AND DIELECTRIC LAYERS AND ETCH THE AI LATER TO COMPLETE THE TRAPS' BOTTOM END CAP ELECTRODES 52 DEPOSIT A SECOND AI LAYER FOR THE TRAPS' CENTRAL ELECTRODES DRY ETCH THE SECOND AI LAYER TO FORM TRAPPING CAVITIES AND COMPLETE THE CENTRAL ELECTRODES - 54 DEPOSIT SACRIFICIAL AMORPHOUS SILICON TO FILL THE CAVITIES IN THE CENTRAL ELECTRODES CMP THE SACRIFICIAL LAYER OF AMORPHOUS SILICON TO PRODUCE A FLAT TOP SURFACE <sub>7</sub> 56 DEPOSIT A THIRD AT LAYER FOR THE TRAPS' TOP END CAP ELECTRODES ON THE FLAT TOP SURFACE r 57 DRY ETCH THE THIRD AI LAYER TO COMPLETE THE TOP END CAP ELECTRODES AND REMOVE EXPOSED OXIDE c 58 DEPOSIT PROTECTIVE LAYER OVER STRUCTURE ON FRONT SURFACE OF WAFER 59 MECHANICAL GRIND BACKSIDE OF THE WAFER TO CONVENIENT **THICKNESS** 60 PERFORM DEEP ETCH VIA THROUGH BACK SURFACE OF WAFER TO EXPOSE BOTTOM END CAP ELECTRODE PERFORM ETCH TO REMOVE SACRIFICIAL MATERIAL FROM THE TRAPPING CAVITIES AND PORTS THERETO

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FIG. 6

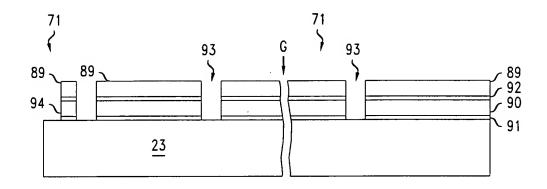


FIG. 7

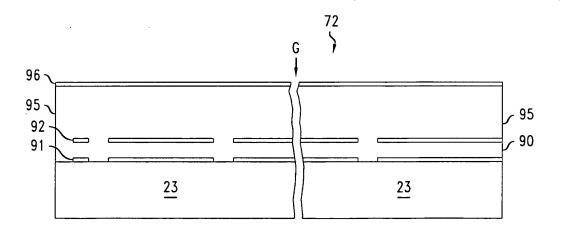
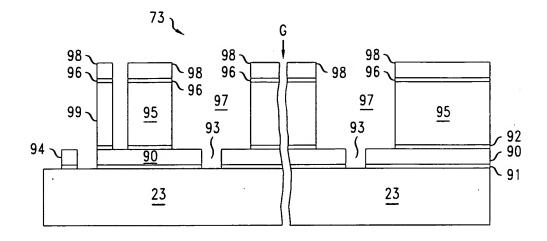


FIG. 8



*FIG.* 9

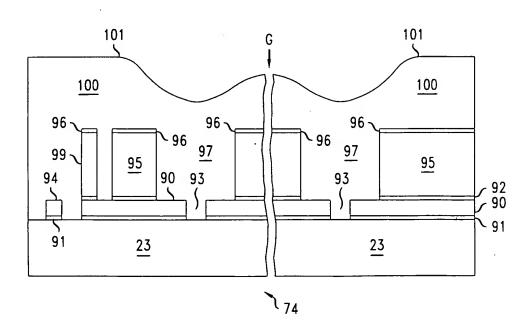


FIG. 10

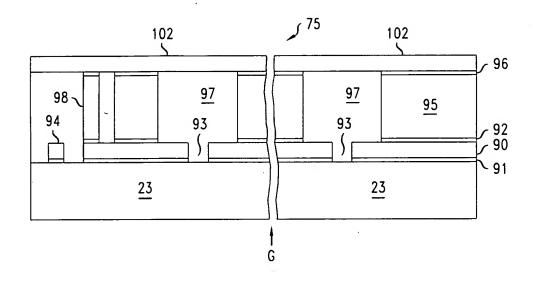


FIG. 11

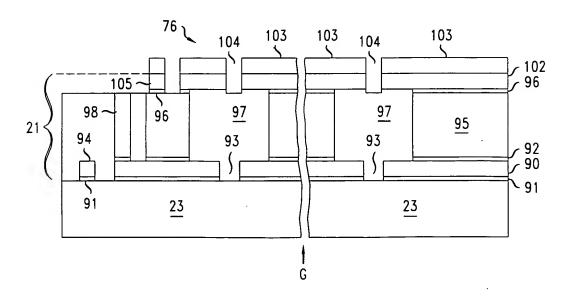


FIG. 12

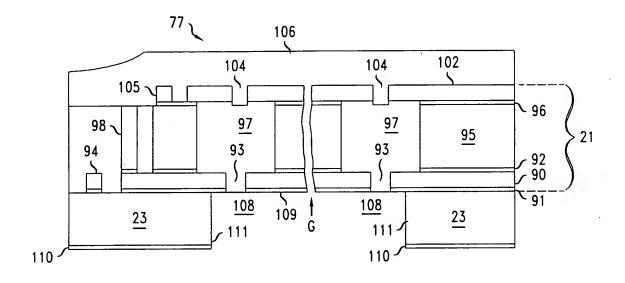


FIG. 13

